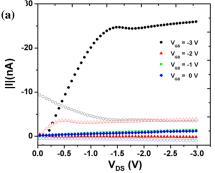
Electronic Supplementary Material (ESI) for Physical Chemistry Chemical Physics.

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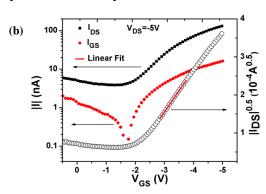
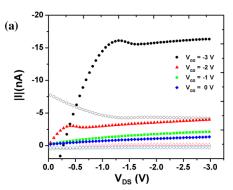


Figure S1: (a) Output characteristics ( $I_{DS} \times V_{DS}$ ) of the transistor with untreated cr-PVA layer. Open symbols correspond to leakage current ( $I_{GS}$ ), whereas solid symbols represent channel current ( $I_{DS}$ ); (b) transfer characteristics of the same device.



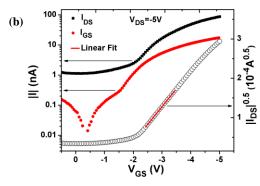
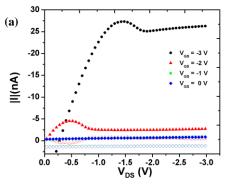


Figure S2: (a) Output characteristics ( $I_{DS} \times V_{DS}$ ) of the transistor in which the cr-PVA layer was treated with 0.3 mg/mL of CTAB solution. Open symbols correspond to leakage current ( $I_{GS}$ ), whereas solid symbols represent channel current ( $I_{DS}$ ); (b) transfer characteristics of the same device.



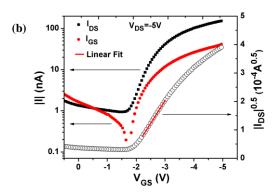
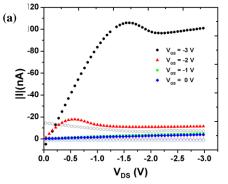


Figure S3: (a) Output characteristics ( $I_{DS} \times V_{DS}$ ) of the transistor in which the cr-PVA layer was treated with 0.5 mg/mL of CTAB solution. Open symbols correspond to leakage current ( $I_{GS}$ ), whereas solid symbols represent channel current ( $I_{DS}$ ); (b) transfer characteristics of the same device.



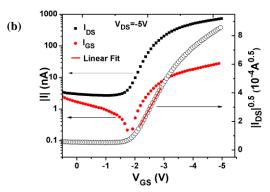


Figure S4: (a) Output characteristics ( $I_{DS} \times V_{DS}$ ) of the transistor in which the cr-PVA layer was treated with 3.0 mg/mL of CTAB solution. Open symbols correspond to leakage current ( $I_{GS}$ ), whereas solid symbols represent channel current ( $I_{DS}$ ); (b) transfer characteristics of the same device.